🐯 McGill		Microwave Electronics 573
A: Tunnel Diodes	ECSE-573	September 2006
[1] Introduction		
[2] Qualitative description of tu	unnel diode	
Cross- section, doping distribution, electric field distribution		
[3] Qualitative description of current- voltage characteristics		
[4] Degenerate semiconductors and Fermi levels		
[5] Tunneling probability		
[6] Current-voltage characteristics and negative differential resistivity		
[7] Oscillators utilizing tunnel diodes		
[8] Small signal equivalent circ	cuits	
[9] Fabrication techniques		
[10] A survey of manufacturers of the tunnel diodes and a summary on the evolution of development of tunnel diodes for microwave and millimeter-wave applications		
[11] Examples of commercial p microwave frequencies	products involving	the tunnel diodes at
Fall 2006		1

() MCGIII	Microwave Electronics 573	
Presentation package A-1: items [1] to [6]	(Hadley, 09/21)	
Presentation package A-2: items [7] to [11]	(Qing, 09/26)	
	Cheduled Date	
 Every presentation is scheduled to be 45 minutes, followed by a discussion period. (Students are encouraged to participate in the discussion period) Each class will have one presentations. 		
 Every presentation is scheduled to be 45 min period. (Students are encouraged to participa) Each class will have one presentations. 	nutes , followed by a discussion te in the discussion period)	
 Every presentation is scheduled to be 45 mir period. (Students are encouraged to participa) Each class will have one presentations. Deadline to hand in presentation slides for A 	nutes , followed by a discussion ite in the discussion period) -1: Sept. 20 th	
 Every presentation is scheduled to be 45 min period. (Students are encouraged to participate Each class will have one presentations. Deadline to hand in presentation slides for A Deadline to hand in presentation slides for A 	 hutes, followed by a discussion te in the discussion period) -1: Sept. 20th -2: Sept. 25th 	
 Every presentation is scheduled to be 45 mir period. (Students are encouraged to participa Each class will have one presentations. Deadline to hand in presentation slides for A Deadline to hand in presentation slides for A 	 hutes, followed by a discussion te in the discussion period) -1: Sept. 20th -2: Sept. 25th 	
 Every presentation is scheduled to be 45 mir period. (Students are encouraged to participa Each class will have one presentations. Deadline to hand in presentation slides for A Deadline to hand in presentation slides for A 	 hutes, followed by a discussion te in the discussion period) -1: Sept. 20th -2: Sept. 25th 	
 Every presentation is scheduled to be 45 mir period. (Students are encouraged to participa Each class will have one presentations. Deadline to hand in presentation slides for A Deadline to hand in presentation slides for A 	 hutes, followed by a discussion te in the discussion period) -1: Sept. 20th -2: Sept. 25th 	



🕏 McGill	Microwave Electronics 573
Presentation package B-1: items [1] to [6] (Guillau Presentation package B-2: items [7] to [11] (Li,	me, 09/28) 10/03) T Scheduled Date
 Every presentation is scheduled to be 45 minutes, period. (Students are encouraged to participate in the Each class will have one presentations. Deadline to hand in presentation slides for B-1: Set Deadline to hand in presentation slides for B-2: O 	followed by a discussion he discussion period) ept. 27 th oct. 2 nd
Fall 2006	4

the second secon	Microwave Electronics 573			
C: Transferred electron devices ECSE-573	September 2006			
[1] Introduction				
[2] Qualitative description of transferred electron devices				
Cross- section, doping distribution, electric field distribution				
[3] Bulk negative differential resistivity, spacial response, temporal response				
[4] N-shaped and S-shaped bulk negative differential resistivity				
[5] Formation of high field domain				
[6] Dipole layer for N-shaped devices				
[7] Current-controlled negative differential resistivity devices				
[8] Energy required for transferred electron effects				
[9] Modes of operation (Ideal uniform-field mode, Accumulation-layer mode, Transit-time dipole-layer mode)				
[10] Excess voltage and load line (device line)				
[11] Triangular domain formation and fundament	al frequency			
[12] Comparison of different operation modes				
[13] Equivalent circuits (Bosch, Gunn effect elect	tronics)			
Fall 2006	5			

🐯 McGill	Microwave Electronics 573
C: Transferred electron devices (continue)	
[14] Impedance for low field region	
[15] Impedance for high field region	
[16] Power-frequency performance	
[17] Some examples of Gunn device applications	
[18] A comprehensive survey on the development of T	ГEDs
[19] A survey on the manufacturers of microwave and circuits involving TEDs	l millimeter wave
[20] Evolution of the microwave and millimeter wave TEDs	markets involving
Fall 2006	6

₿ McGill	Microwave Electronics 573	
Presentation package C-1: items [1] to [5] (Hadley, Presentation package C-2: items [6] to [10] (Qing, Presentation package C-3: items [11] to [15](Guillaume, Presentation package C-4: items [16] to [20](Li,	10/05) 10/12) 10/17) 10/19) 10/19) 10/19 Scheduled Date	
 Every presentation is scheduled to be 45 minutes, followed by a discussion period. (Students are encouraged to participate in the discussion period) Each class will have one presentations. Deadline to hand in presentation slides for C-1: Oct. 4th Deadline to hand in presentation slides for C-2: Oct. 11th Deadline to hand in presentation slides for C-3: Oct. 16th Deadline to hand in presentation slides for C-4: Oct. 18th 		
Fall 2006	7	